

40V N-Channel MOSFETs

General Description

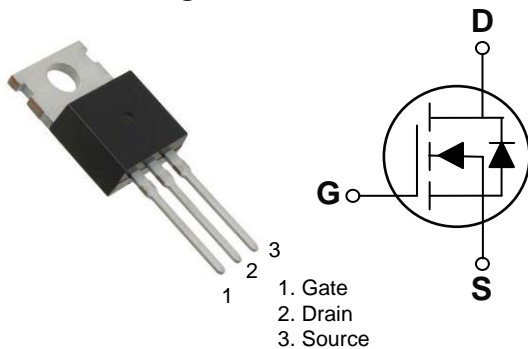
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R _{DS(ON)}	ID
40V	3.8mΩ	150A

Features

- 40V, 150A, R_{DS(ON)} = 3.8mΩ @ V_{GS} = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

TO-220 Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	± 20	V
I _D	Drain Current – Continuous (T _C =25°C)	150	A
	Drain Current – Continuous (T _C =100°C)	95	A
I _{DM}	Drain Current – Pulsed ¹	600	A
EAS	Single Pulse Avalanche Energy ²	312	mJ
IAS	Single Pulse Avalanche Current ²	79	A
P _D	Power Dissipation (T _C =25°C)	166	W
	Power Dissipation – Derate above 25°C	1.33	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	62	°C/W
R _{θJC}	Thermal Resistance Junction to Case	---	0.75	°C/W



FTK4960P

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.03	---	V/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance ³	$V_{GS}=10V, I_D=25A$	---	3.1	3.8	m Ω
		$V_{GS}=4.5V, I_D=12A$	---	4.0	5.0	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	mV/ $^\circ\text{C}$
gfs	Forward Transconductance	$V_{DS}=10V, I_D=2A$	---	16	---	S

Dynamic Characteristics

Q_g	Total Gate Charge ^{3,4}	$V_{DS}=20V, V_{GS}=4.5V, I_D=10A$	---	44.4	80	nC
Q_{gs}	Gate-Source Charge ^{3,4}		---	9.6	18	
Q_{gd}	Gate-Drain Charge ^{3,4}		---	16	30	
$T_{d(on)}$	Turn-On Delay Time ^{3,4}	$V_{DD}=20V, V_{GS}=10V, R_G=6\Omega, I_D=1A$	---	28	50	ns
T_r	Rise Time ^{3,4}		---	3.2	6.5	
$T_{d(off)}$	Turn-Off Delay Time ^{3,4}		---	89	160	
T_f	Fall Time ^{3,4}		---	14	28	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	4940	7800	pF
C_{oss}	Output Capacitance		---	425	800	
C_{rss}	Reverse Transfer Capacitance		---	170	330	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.4	2.8	Ω

Drain-Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	150	A
I_{SM}	Pulsed Source Current ³		---	---	300	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=79A$, Starting $T_J=25^\circ\text{C}$
3. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

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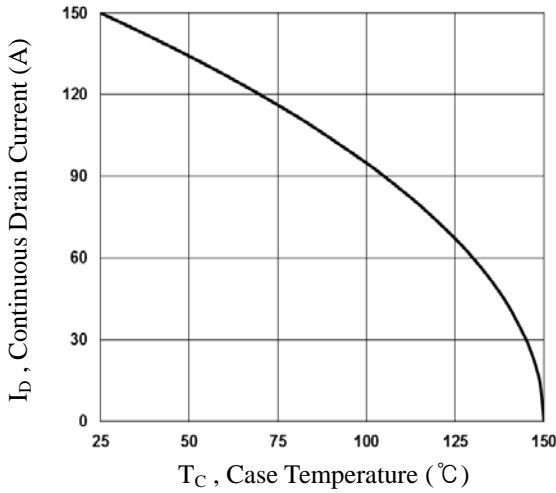


Fig.1 Continuous Drain Current vs. T_c

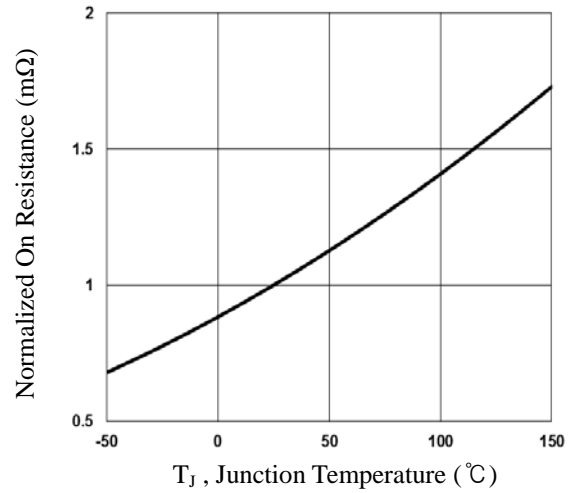


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

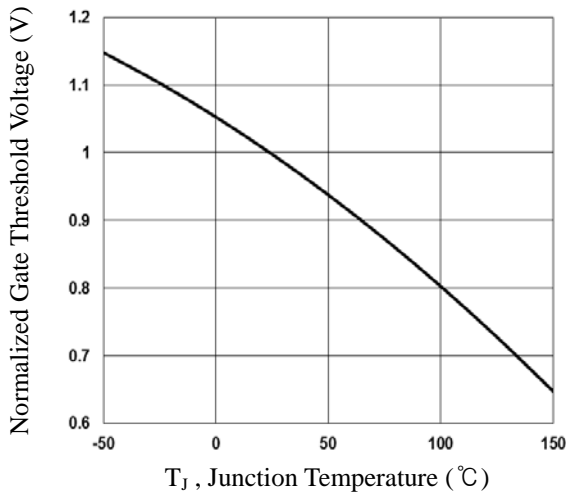


Fig.3 Normalized V_{th} vs. T_j

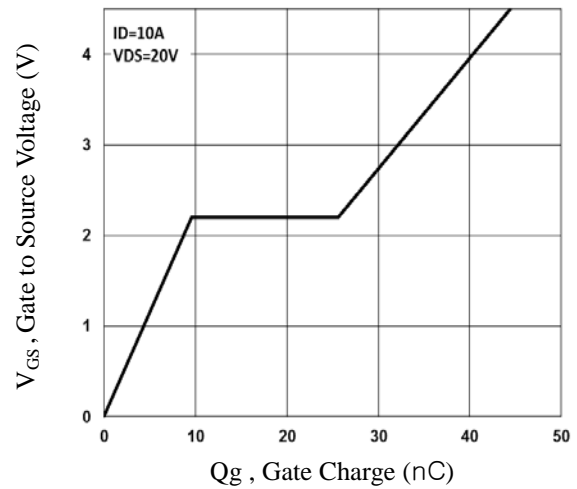


Fig.4 Gate Charge Waveform

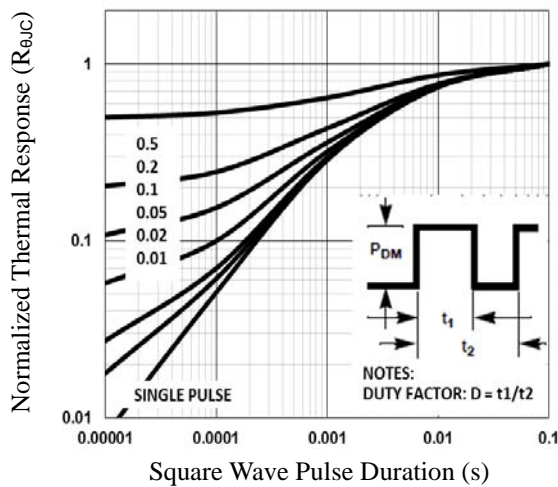


Fig.5 Normalized Transient Impedance

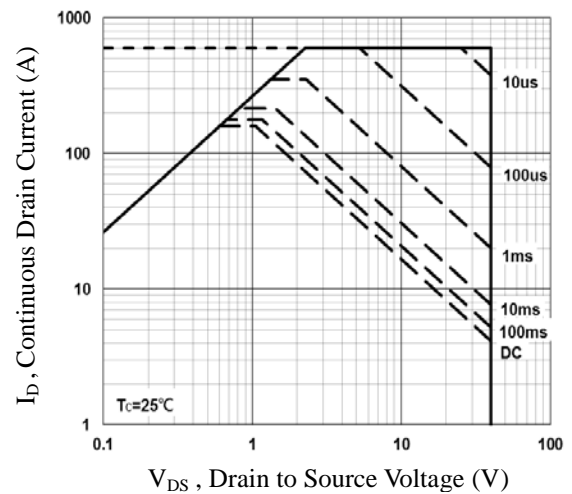


Fig.6 Maximum Safe Operation Area



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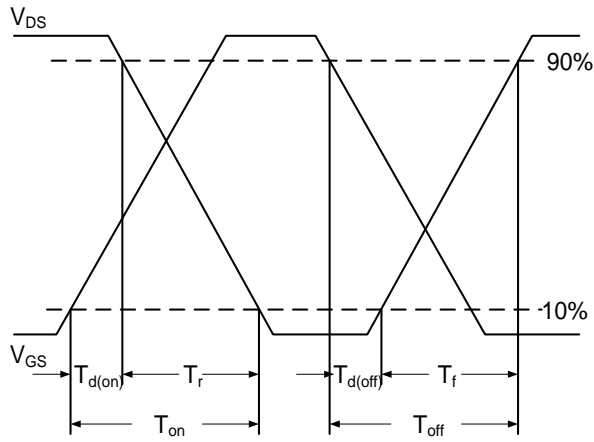


Fig.7 Switching Time Waveform

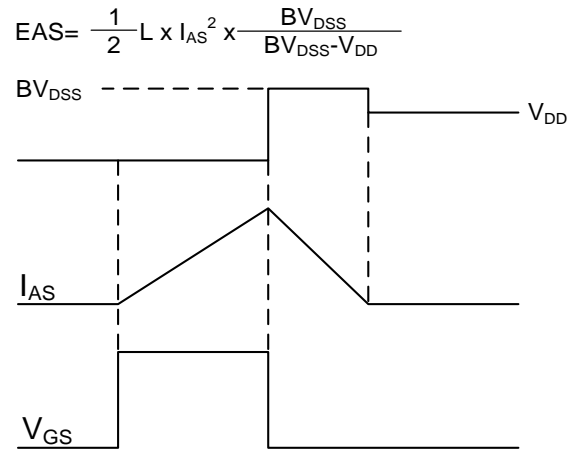
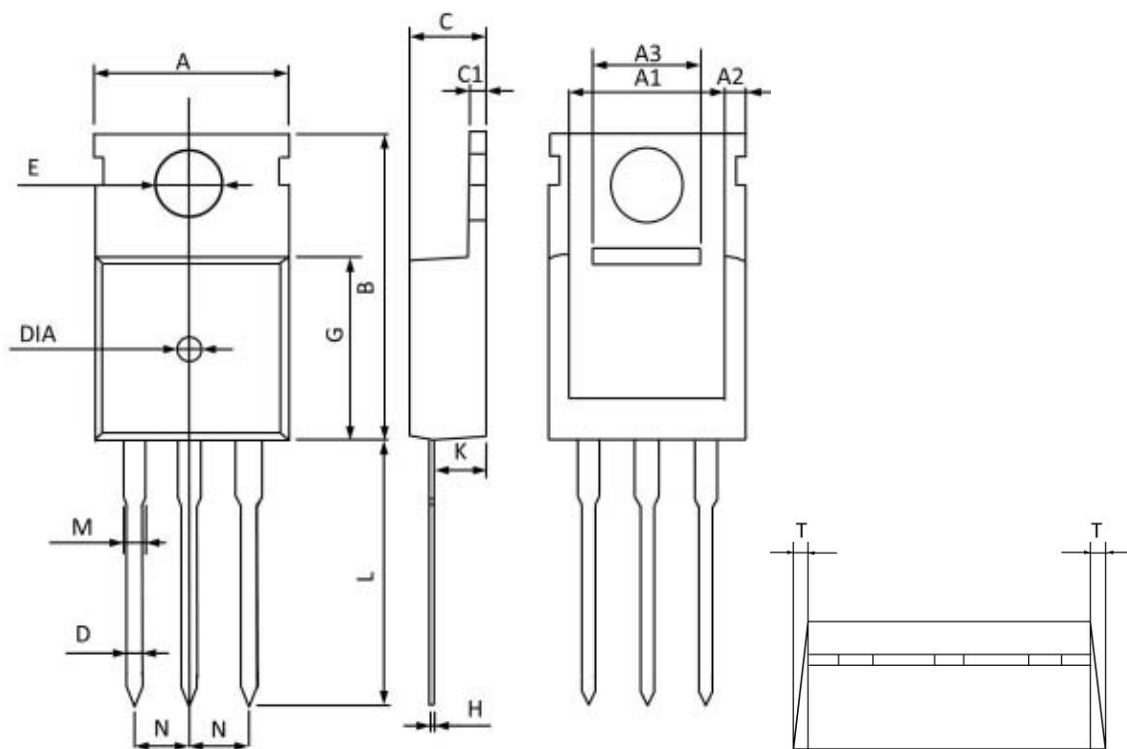


Fig.8 EAS Waveform

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TO-220 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.300	9.700	0.406	0.382
A1	8.840	8.440	0.348	0.332
A2	1.250	1.050	0.049	0.041
A3	5.300	5.100	0.209	0.201
B	16.200	15.400	0.638	0.606
C	4.680	4.280	0.184	0.169
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	3.800	3.400	0.150	0.134
G	9.300	8.700	0.366	0.343
H	0.600	0.400	0.024	0.016
K	2.700	2.100	0.106	0.083
L	13.600	12.800	0.535	0.504
M	1.500	1.100	0.059	0.043
N	2.590	2.490	0.102	0.098
T	W0.35		W0.014	
DIA	Φ1.5 TYP.	deep0.2 TYP.	Φ0.059 TYP.	deep0.008 TYP.